

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC3893

DESCRIPTION

- With TO-3P(H)IS package
- Built-in damper diode
- High voltage ,high speed

APPLICATIONS

- Horizontal deflection output for high resolution display

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

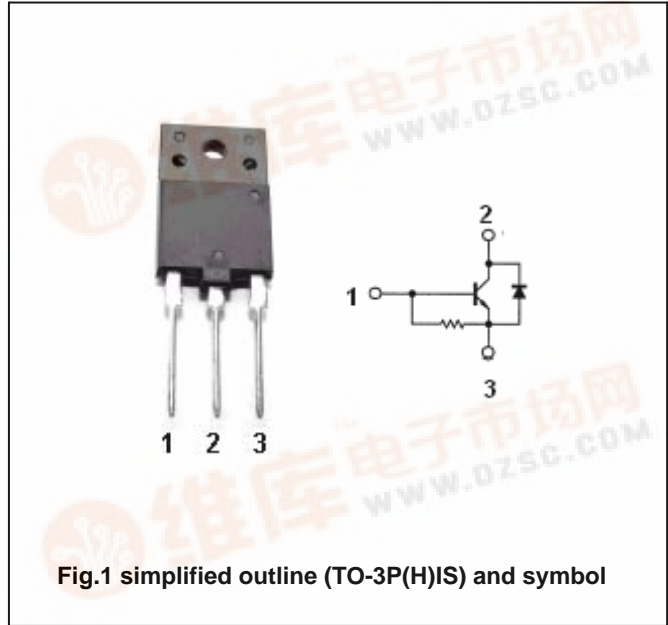


Fig.1 simplified outline (TO-3P(H)IS) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1400	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		15	A
I _B	Base current		4	A
P _C	Collector power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =200mA, I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.5A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.5A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0	66		200	mA
h _{FE}	DC current gain	I _C =1A; V _{CE} =5V	8	12		
f _T	Transition frequency	I _C =0.1A; V _{CE} =10V	1	3		MHz
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =10V; f=1MHz		210		pF
V _F	Diode forward voltage	I _F =6A			2.0	V
t _s	Storage time	Resistive load I _{CP} =6A; I _{B1} =1.2A; I _{B2} =-2.4A R _L =33.3Ω			2.5	μs
t _f	Fall time				0.2	μs

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PACKAGE OUTLINE

